From measurements of the photoresponse, as a function of wavelength, of a number of GaAs p si -n diodes (3 different si crystals) in the range from 2.1μ to 0.76 μ , we conclude that the level E_R lies between 0.75 and 0.8 eV below the conduction band. This is near the level in si GaAs which has been attributed to oxygen and which plays a role in making GaAs semi-insulating. Similar measurements on various Si units have given values for E_R near 0.55 eV and near 0.65 eV. The former level fits the known 0.54-eV Au acceptor level in Si; the latter is near an acceptor level thought to be due to Cu. From these measurements, and the initial assumption that Lampert's model fit our experimental results in GaAs and Si, we predicted the Ge unit of Fig. 3 and obtained double injection negative resistance by deliberately introducing Cu into Ge, and presumably the 0.33-eV double Cu acceptor level. The consistency of all of these results (300'K) with Lampert's model, plus the V^2 space-charge-limitedemission electron currents we observe at low currents in GaAs and Si, tends to confirm the general features of Lampert's work, as well as some of the broader ideas first advanced by Stafeev and

until now demonstrated only at low temperatures.

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NUCLEAR MAGNETIC RESONANCE IN MnF₂ NEAR THE CRITICAL POINT^{*}

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The F^{19} nuclear resonance in MnF₂, first observed by Shulman and Jaccarino,^{1,2} has been studied in detail in the very interesting temperature region around the paramagnetic -antiferromagnetic critical temperature $T_N = 67.4$ °K. Our experimental system permits temperature measurement and control to within one millidegree for as long as six hours, any temperature variation across the sample being much less than a millidegree. Temperatures were measured with a platinum resistance thermometer calibrated very carefully using the vapor pressure-temperature curve for nitrogen.³ An inductive coupling arrangement used gen. An mauctive coupling arrangement used
with a very high frequency spectrometer,⁴ plus a standard Pound-Knight-Watkins spectrometer, made possible nuclear magnetic resonance observations at frequencies from 23 to 110 Mc/sec without making any changes inside the low-temperature apparatus. Nuclear resonances of width up to 3 Mc/sec could be detected with this system.

We have determined the temperature dependence of the F^{19} resonance frequency ν_{19} in zero applied field in the antiferromagnetic state between T_N and 52°K. Our data start at $T = T_N - 0.005K^{\circ}$ at which temperature v_{19} is about 8 Mc/sec. This frequency corresponds to a reduction of the sublattice magnetization to 5% of the magnetization at absolute zero. For the first few degrees below the Néel point, the data very accurately fit the expression

$$
\frac{M(T)}{M(0)} = \frac{\nu_{19}(T)}{\nu_{19}(0)} = A (T_N - T)^{R},
$$
\n(1)

FIG. 1. Temperature dependence of the cube of the F^{19} nuclear resonance frequency for the first 1.8 degrees below T_N . The points lie on the straight line shown to within the experimental uncertainty of about 5 millidegrees.

where $R = 0.335 \pm 0.01$, $A = (0.295 \pm 0.001)(K^{\circ})^{-R}$. and $v_{19}(0) = 159.978$ Mc/sec. The accuracy with which Eq. (1) fits the data can be seen in Fig. 1 which plots $v_{19}(T)$ versus the temperature for the first 1.8 degrees below T_N . Extrapolation over the last 5 millidegrees enables us to determine that

$$
T_{\rm M} = (67.336 \pm 0.003)^{\circ} \text{K}.
$$
 (2)

Since Eq. (1) does not have the correct asymptotic behavior as $T \rightarrow 0$, it cannot be expected to hold far below T_N . The experimental results depart from the values given by Eq. (1) by $0.02K^{\circ}$, $0.10K^{\circ}$, and $0.5K^{\circ}$ at $61^{\circ}K$, $58.5^{\circ}K$, and $53^{\circ}K$, respectively. The experimental data for the range $52^\circ K \leq T \leq T_N$ are plotted in Fig. 2. The cube root law that we observe shows that the sublattice magnetization rises much faster than the law $M \propto (T_N - T)^{1/2}$ predicted by the molecular field theory just below T_N . The molecular field theory prediction is shown together with our data for $v_{19}(T)$ in Fig. 2. The precision of the nuclear resonance measurements, as illustrated in Figs. 1 and ² and Eq. (1), demonstrates the power of this method^{5,6} in determining the sublattice magnetization in the theoretically difficult, but important, critical region.

By observing the shift of the nuclear resonances on applying a magnetic field H_0 along the C (antiferromagnetic) axis, we were able to determine the susceptibility $\chi_{\,\parallel\,}$ for each of the two Mn $^{++}$

sublattices separately near T_N . The susceptibilities of the up and down sublattices were found to be equal and their sum is in good agreement with the ordinary macroscopic susceptibility measurements. ⁷

In the antiferromagnetic state the F^{19} linewidths are strongly anisotropic, depending on the direction of the vector sum \widetilde{H}_{nucl} of the applied field and the field produced by the Mn⁺⁺ spins at the \mathbf{F}^{19} nucleus. The lines are broadest for $\mathbf{\tilde{H}}_{\text{nucl}}$ along C and narrowest for \widetilde{H}_{nucl} along A. (See Fig. 3.) For $\overline{H}_{\text{nucl}}$ along C, the linewidth is given to within 20% by

$$
\delta \nu_C = 490 \left[\text{kc/sec} \left(\text{K}^{\circ} \right)^{1/2} \right] \left(T_N - T \right)^{-1/2};
$$

0.02K^o < T_N - T < 15K^o. (3)

In this 15-degree temperature range the linewidth increases from 100 kc/sec to 3000 kc/see. In the paramagnetic state the line shows an extraordinarily rapid broadening as T_N is approached. The broadening is anisotropic, being more marked at a given temperature with the applied field along C than along A. (See Fig. 4.) For $0.04K^{\circ} < T - T_N$ $~10K^{\circ}$ the linewidths are given to within 15% by H_0 along C: $\delta \nu_C = 95 \text{ kc/sec} [1 + 0.33 \text{K}^{\circ}/(T - T_N)],$ H_0 along A: $\delta v_A = 85 \text{ kc/sec} [1 + 0.12 \text{K}^{\circ}/(T - T_N)].$ (4)

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FIG. 2. Temperature dependence of the F^{19} resonance frequency in the range $52^{\circ}K$ $\langle T \rangle T_N$. The circles greatly exaggerate the size of the experimental uncertainties. The lower curve is computed using the molecular field theory.

FIG. 3. Temperature dependence of the F^{19} linewidths in the antiferromagnetic state. The single point at 4°K is from reference 2.

FIG. 4. Temperature dependence of the F^{19} linewidths in the paramagnetic state just above the Neel point.

Note that in the last degree above T_N the line broadens by about a factor of ten. It has been proposed^{1,8} that the linewidth of the F^{19} resonance is determined by exchange narrowing of the hyperfine interaction between the F^{19} nucleus and the nearest neighbor Mn^{++} spins. If this is the case, the present measurements provide rather direct experimental information on the temperature dependence of the time-space correlation function for the manganese spins in the critical region.

The rapid fade-out of the line which accompanies this broadening provides an extremely sensitive method for measuring changes in the Neel temperature. In particular we have measured the depression of the Neel temperature due to an applied field. In Table I we list the results obtained, together with the predicted Neel point shifts on the molecular field model. We have also measured the effect of hydrostatic pressure on T_{N} . Our result,

$$
dT_N/dP = 303 \pm 3 \text{ millidegrees per } 1000 \text{ kg/cm}^2,
$$
\n(5)

Table I. Effect on T_N of raising applied field H_0 from 5.4 kG to 8.²⁵ kG.

	ΔT _N in millidegrees	
Field direction	Expt.	Mol. field theory
A axis	-2.8 ± 1	-0.87
C axis	-7.5 ± 1	-2.6

agrees well with the estimate of Benedek and Kushida4 obtained by a quite different method. The pressure dependence of T_N shows that the Néel point is itself a function of the temperature because of the effect of thermal expansion. Using our pressure data and the thermal expansion measurements of Gibbons,⁹ we have estimated the importance of this effect in fitting the $v_{19}(T)$ data to Eq. (1) with $T_N = T_N(T)$. Our estimate shows that, with this correction, the coefficient A in (1) should be about one percent less than stated above. The effect on the exponent R is negligible.

Just below T_N we observe, to our surprise, lines corresponding to nuclei in both the antiferromagnetic and paramagnetic phases, the line at the paramagnetic location fading rapidly with decreasing temperature and disappearing entirely at about 25 millidegrees below T_N . At 5 millidegrees below T_N the areas under the two lines are roughly equal. We do not understand this effect. One obvious possibility is that it is due to an inhomogeneity in the sample's Neel temperature caused, perhaps, by internal strains. Such a mechanism would broaden the line below T_N . However, the actual linewidths for \widetilde{H}_{nucl} along A. are several times larger than possible for such a mechanism. Furthermore, the linewidths for H_{nuc} along C fall off more slowly as the temperature is reduced than can be predicted on this basis.

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MICROWAVE GENERATION IN RUBY DUE TO POPULATION INVERSION PRODUCED BY OPTICAL ABSORPTION

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Microwave amplification and generation by the stimulated emission of radiation (maser) were observed in ruby as a result of population inversion produced, in the ground state of Cr^{3+} by the absorption of the coherent optical emission from a second ruby (optical maser). The maser crystal was oriented in a magnetic field of about 6700 Oe to obtain a transition between a ground 4A_2 Zeeman sublevel and an excited $\overline{E}({}^2E)$ Zeeman sublevel which would match a spectral component of the output of the optical maser. The arrangement of the experimental apparatus is shown schematically in Fig. 1.

Detection of the interaction of optical and para-

FIG. 1. Arrangement of experimental apparatus.